Thyristors BT145 series

# **GENERAL DESCRIPTION**

# Glass passivated thyristors in a plastic envelope, intended for use in applications requiring high bidirectional blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

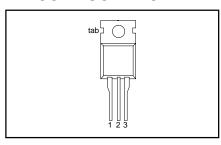
### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
	BT145-	500R	600R	800R	
$egin{array}{c} egin{array}{c} \egin{array}{c} \egin{array}{c} \egin{array}{c} \egin{array}$	Repetitive peak off-state voltages	500	600	800	V
I <sub>T(AV)</sub>	Average on-state current	16	16	16	Α
I <sub>T(RMS)</sub>	RMS on-state current Non-repetitive peak on-state	25 300	25 300	25 300	A
I SIVI	current				

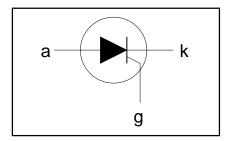
# **PINNING - TO220AB**

ſ	PIN	DESCRIPTION			
	1	cathode			
	2	anode			
	3	gate			
	tab	anode			

# **PIN CONFIGURATION**



# **SYMBOL**



# **LIMITING VALUES**

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.		MAX.		UNIT
$V_{DRM}$ , $V_{RRM}$	Repetitive peak off-state voltages		-	<b>-500R</b> 500 <sup>1</sup>	<b>-600R</b> 600 <sup>1</sup>	<b>-800R</b> 800	V
I <sub>T(AV)</sub> I <sub>T(RMS)</sub> I <sub>TSM</sub>	Average on-state current RMS on-state current Non-repetitive peak on-state current	half sine wave; $T_{mb} \le 101  ^{\circ}\text{C}$ all conduction angles half sine wave; $T_{j} = 25  ^{\circ}\text{C}$ prior to surge	-		16 25		A A
l²t dl <sub>⊤</sub> /dt	I <sup>2</sup> t for fusing Repetitive rate of rise of	t = 10  ms t = 8.3  ms t = 10  ms $I_{TM} = 50 \text{ A}$ ; $I_G = 0.2 \text{ A}$ ;	- - -		300 330 450 200		Α Α Α²s Α/μs
I <sub>GM</sub> V <sub>GM</sub> V <sub>RGM</sub> P <sub>GM</sub> P <sub>GM</sub>	on-state current after triggering Peak gate current Peak gate voltage Peak reverse gate voltage Peak gate power Average gate power	$dI_{G}/dt = 0.2 \text{ A/}\mu\text{s}$ over any 20 ms period			5 5 5 20 0.5		A > > W W
$T_{stg}^{G(AV)}$	Storage temperature Operating junction temperature	over any 20 ms penou	-40 -		150 125		ပံ့ပွဲ

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<sup>1</sup> Although not recommended, off-state voltages up to 800V may be applied without damage, but the thyristor may switch to the on-state. The rate of rise of current should not exceed 15 A/ $\mu$ s.

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# THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R <sub>th j-mb</sub>	Thermal resistance		-	-	1.0	K/W
R <sub>th i-a</sub>	junction to mounting base Thermal resistance junction to ambient	in free air	-	60	-	K/W

# STATIC CHARACTERISTICS

 $T_j = 25$  °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>GT</sub>	Gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$	-	5	35	mA
l IĽ	Latching current	$V_{\rm D} = 12 \text{ V}; I_{\rm GT} = 0.1 \text{ A}$	-	25	80	mA
I <sub>H</sub>	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	-	20	60	mA
Ϊ́Τ	On-state voltage	$I_{T} = 30 \text{ A}$	-	1.1	1.5	V
V <sub>GT</sub>	Gate trigger voltage	$\dot{V}_{D} = 12 \text{ V}; I_{T} = 0.1 \text{ A}$	-	0.6	1.0	V
		$V_D = V_{DRM(max)}$ ; $I_T = 0.1 \text{ A}$ ; $T_j = 125 ^{\circ}\text{C}$	0.25	0.4	-	V
$I_D, I_R$	Off-state leakage current	$V_D = V_{DRM(max)}$ ; $V_R = V_{RRM(max)}$ ; $T_j = 125$ °C	-	0.2	1.0	mA

# **DYNAMIC CHARACTERISTICS**

 $T_i = 25$  °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV <sub>D</sub> /dt	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM(max)}; T_j = 125 °C;$ exponential waveform; gate open circuit	200	500	-	V/μs
t <sub>gt</sub>	Gate controlled turn-on time	$I_{TM} = 40 \text{ A}; V_D = V_{DRM(max)}; I_G = 0.1 \text{ A};$ $dI_C/dt = 5 \text{ A}/us$	-	2	-	μs
t <sub>q</sub>	Circuit commutated turn-off time	$V_D = 67\% \ V_{DRM(max)}; \ T_j = 125 \ ^{\circ}C; \ I_{TM} = 50 \ A; \ V_R = 25 \ V; \ dI_{TM}/dt = 30 \ A/\mu s; \ dV_D/dt = 50 \ V/\mu s$	-	70	-	μs

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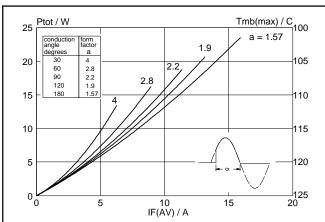


Fig.1. Maximum on-state dissipation,  $P_{tot}$ , versus average on-state current,  $I_{T(AV)}$ , where a = form factor =  $I_{T(RMS)}$ /  $I_{T(AV)}$ .

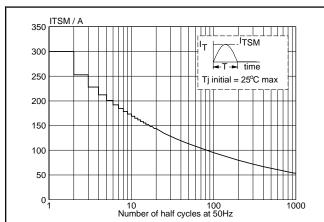


Fig.4. Maximum permissible non-repetitive peak on-state current I<sub>TSM</sub>, versus number of cycles, for sinusoidal currents, f = 50 Hz.

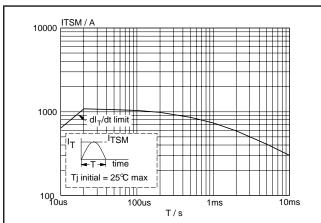


Fig.2. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus pulse width  $t_p$ , for sinusoidal currents,  $t_p \le 10$ ms.

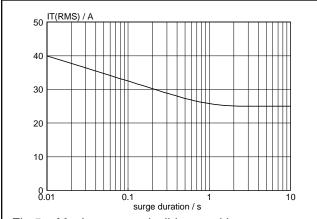


Fig.5. Maximum permissible repetitive rms on-state current  $I_{T(RMS)}$ , versus surge duration, for sinusoidal currents, f = 50 Hz;  $T_{mb} \le 101$  °C.

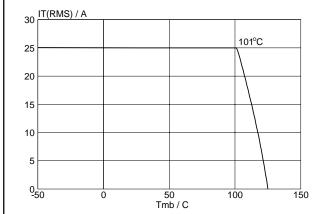


Fig.3. Maximum permissible rms current I<sub>T(RMS)</sub>, versus mounting base temperature  $T_{mb}$ .

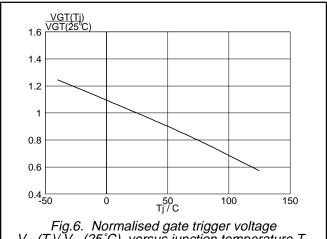
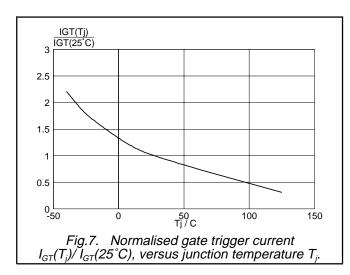
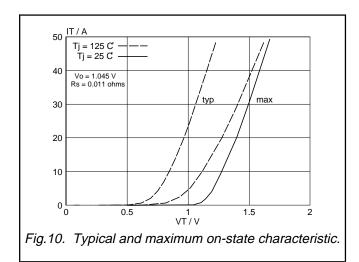


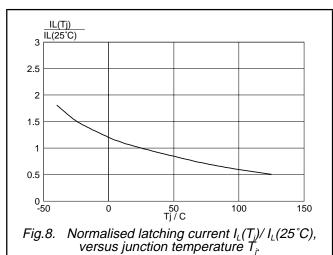
Fig.6. Normalised gate trigger voltage  $V_{GT}(T_j)/V_{GT}(25^{\circ}C)$ , versus junction temperature  $T_{j^{\circ}}$ 

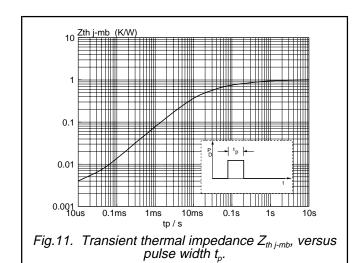
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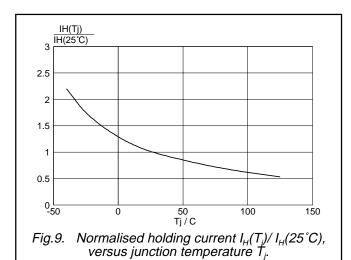
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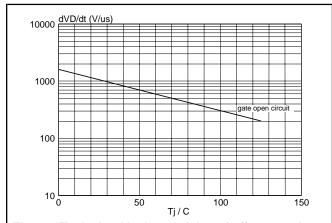
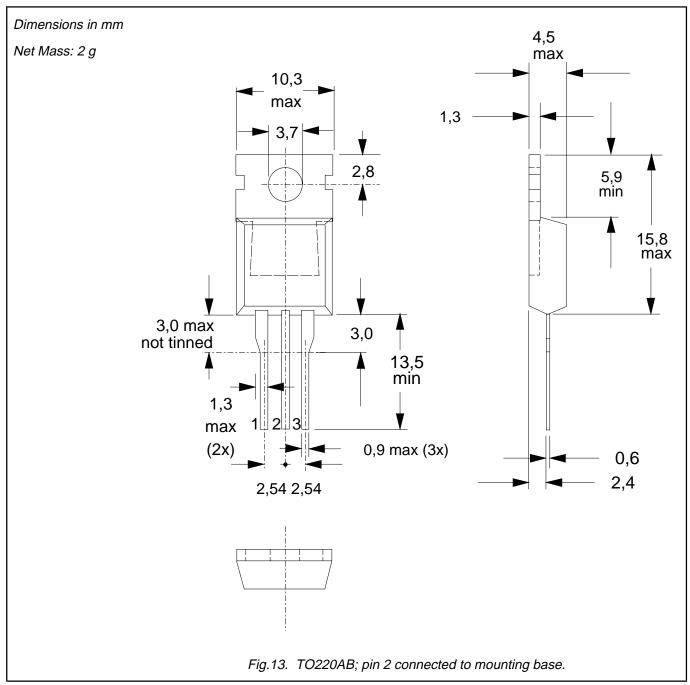


Fig.12. Typical, critical rate of rise of off-state voltage, dV<sub>D</sub>/dt versus junction temperature T<sub>j</sub>.

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# **MECHANICAL DATA**



- Notes
  1. Refer to mounting instructions for TO220 envelopes.
  2. Epoxy meets UL94 V0 at 1/8".

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### **DEFINITIONS**

Data sheet status						
This data sheet contains target or goal specifications for product development.						
This data sheet contains preliminary data; supplementary data may be published later.						
This data sheet contains final product specifications.						
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### Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

#### **Application information**

Where application information is given, it is advisory and does not form part of the specification.

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